

FILE 'USPAT' ENTERED AT 17:07:33 ON 15 JUN 1999

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* * * * *
*       U. S.   P A T E N T   T E X T   F I L E       *
*
* THE WEEKLY PATENT TEXT AND IMAGE DATA IS CURRENT    *
* THROUGH June 15, 1999.                               *
*
* * * * *

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=> s amorphous(w)silicon(w)carbide(4w)gate

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        66285 AMORPHOUS
        204090 SILICON
        65346 CARBIDE
        218161 GATE

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L5 1 AMORPHOUS (W) SILICON (W) CARBIDE (4W) GATE

=> d his

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      (FILE 'USPAT' ENTERED AT 17:02:27 ON 15 JUN 1999)
L1      1 S AMORPHOUS (W) SILICON (W) CARBIDE (2W) GATE

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      FILE 'JPO' ENTERED AT 17:06:55 ON 15 JUN 1999
L2      0 S AMORPHOUS (W) SILICON (W) CARBIDE (2W) GATE
L3      0 S AMORPHOUS (W) SILICON (W) CARBIDE (3W) GATE
L4      0 S AMORPHOUS (W) SILICON (W) CARBIDE (4W) GATE

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      FILE 'USPAT' ENTERED AT 17:07:33 ON 15 JUN 1999
L5      1 S AMORPHOUS (W) SILICON (W) CARBIDE (4W) GATE

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=> d cit 1-

1. 4,849,797, Jul. 18, 1989, Thin film transistor; Yasuhiro Ukai, et al., 257/57, 77 [IMAGE AVAILABLE]